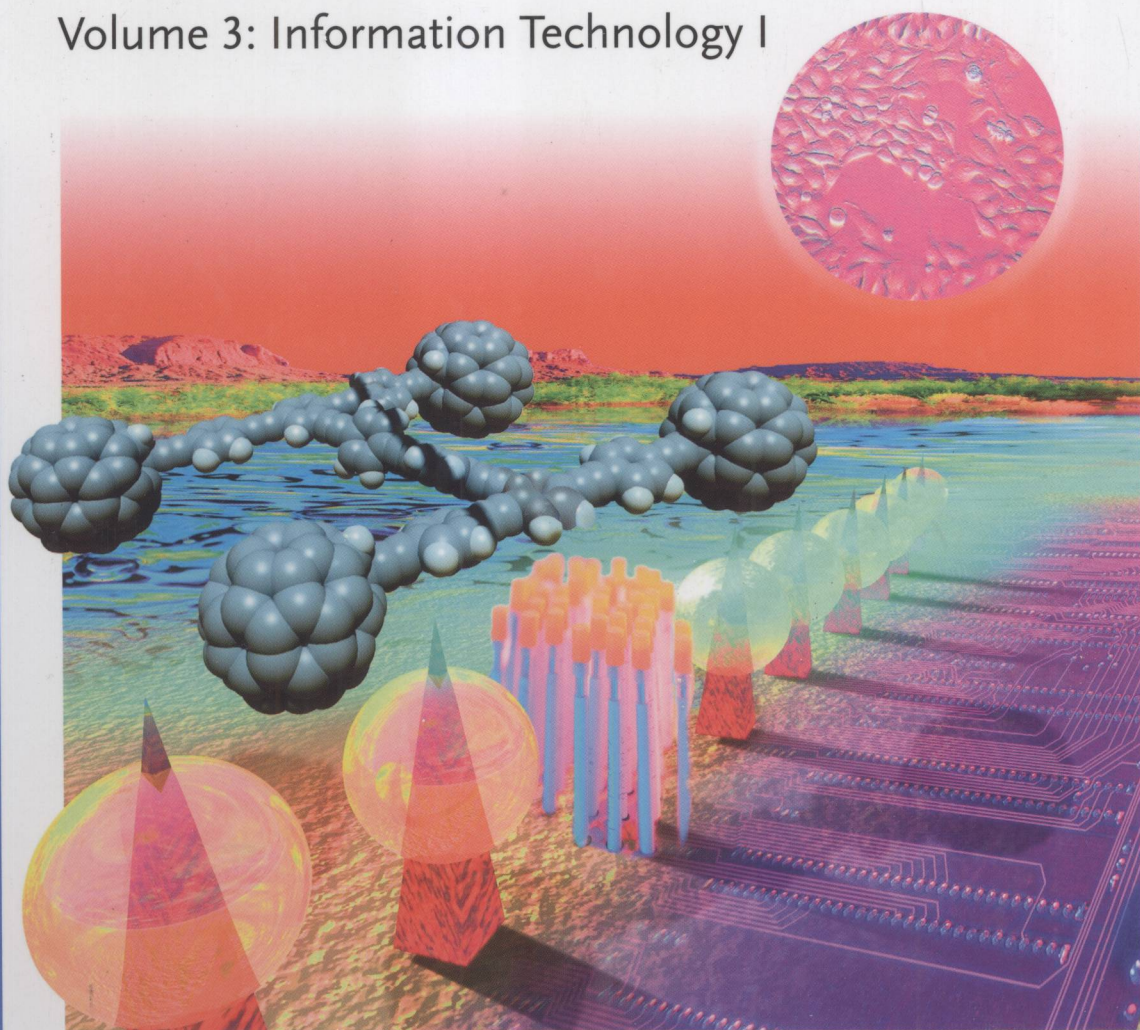


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Preface

Beyond any doubt, Information Technology constitutes the area in which nanotechnology is most advanced. Since its origination during the 1960s, semiconductor technology as the driving force of information technology has advanced and continues to advance at an exponential pace. Today, semiconductor-based information technology penetrates almost all areas of contemporary society – and we are still only at the beginning of a new era. Within the coming decades completely new applications may emerge such as personal real-time translation systems, fully automatic navigation systems for cars, intelligent software agents for the internet, and autonomous robots to assist in our daily lives.

The main ingredient of the tremendous evolution of semiconductor circuitry has been the technological opportunity of ever-shrinking the minimum feature size in the fabrication of semiconductor chips. This led to a corresponding increase in the component density on the chips, decreasing energy consumption of the individual logic and memory cells, as well as higher clock frequencies and the development of multi-core architectures. All this added up to a doubling of the computer performance of chips approximately every 18 months, known as Moore's law. During the first decades of development, semiconductor technology was referred to as *microelectronics*, but this was changed to *nanoelectronics* a few years ago when the minimum feature size was reduced to below 100 nm. At about the same time, the component density has surpassed the one billion per chip mark and continues to progress at an unrestrained pace. Research areas related to nanoelectronics, however, comprise much more than simply the extension of current semiconductor technology to still smaller structures. More importantly, they cover the entire physics of nanosized objects with manifold properties that are unmatched in the macroscopic world and which might one day be exploited to store, to transmit, and to process information. In addition, they deal with technological approaches which are completely different to the *top-down* concept based on lithographical methods. The alternative *bottom-up* concept starts with the chemistry of, for example, organic molecules, nanocrystals, nanotubes, or nanowires, and strives for the self-organization of structures which can themselves act as assemblies of functional

devices. Furthermore, nanoelectronics research investigates completely new computational concepts and architectures.

This text on *Information Technology* within the series *Nanotechnology*, is divided into two volumes and covers the concepts of potential future advances of the semiconductor technology right up to their physical limits, as well as alternative concepts which might one day augment the semiconductor technology, or even replace it in designated areas. Some readers may be familiar with the book *Nanoelectronics and Information Technology* (Wiley-VCH, 2nd edition, 2005) which I have edited. Although the topic of the present book is quite similar, the target is somewhat different. While the first volume represents an advanced text book, the present two volumes emphasize encyclopedic reviews in-line with the concept of the series. Yet, wherever possible, I have strived for a complementarity of the topics covered in the two texts.

This volume covers three parts:

Part One – *Basic Principles and Theory* – includes chapters on the mesoscopic transport of electrons, single electron effects and processes dominated by the electron spin. Furthermore, the fundamental physics of computational elements and its limits are covered.

Part Two – *Nanofabrication Methods* – starts with the prospects of various optical and non-optical lithography techniques, describes the manipulation of nanosized objects by probe methods, and closes with chemistry- and biology-based bottom-up concepts.

Part Three – *High-Density Memories* – begins with an outlook at the future potential of current memories such as Flash and DRAM, attributes magnetoresistive and ferroelectric RAM, and reports about the perspectives of resistive RAM such as phase-change RAM and electrochemical metallization RAM.

Nanotechnology Volume 4 will cover the following topics:

- *Logic Devices and Concepts* – ranges from advanced and non-conventional CMOS devices and semiconductor nanowire device, via various spin-controlled logic devices, and concepts involving carbon nanotubes, organic thin films, as well as single organic molecules, to the visionary idea of intramolecular computation.
- *Architectures and Computational Concepts* – covers biologically inspired structures, and quantum cellular automata, and finalizes by summarizing the main principles and current approaches to coherent solid-state-based quantum computation.

There are many people to whom I owe acknowledgments. First of all, I would like to express my sincere thanks to the authors of the chapters, for their dedication, their patience, and their willingness whenever I requested modifications.

Next, I must pay tribute to the following colleagues (in alphabetical order) for critically reviewing the concept of the text and for their advice on topic and author selection: George Bourianoff (Intel Corp.), Ralph Cavin (Semiconductor Research Corp.), U-In Chung (Samsung Electronics), James Hutchby (Semiconductor Research Corp.), Christoph Koch (Caltech), Phil Kuekes (Hewlett Packard Research Laboratories), Heinrich Kurz (RWTH Aachen University), Rich Liu (Macronix Intl.

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Last – but certainly not least – I was greatly assisted by Dagmar Leisten, who redrew most of the original figures in order to improve their graphical quality, by Thomas Pössinger for his layout work and design ideas aiming at a more consistent appearance of the book, and by Maria Garcia for all the organizational work around such a project and for her sustained support.

Aachen, January 2008

Rainer Waser

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Contents

Preface XV

List of Contributors XIX

I	Basic Principles and Theory	1
1	Phase-Coherent Transport	3
	<i>Thomas Schäpers</i>	
1.1	Introduction	3
1.2	Characteristic Length Scales	4
1.2.1	Elastic Mean Free Path	4
1.2.2	Inelastic Mean Free Path	5
1.2.3	Phase-Coherence Length	5
1.2.4	Transport Regimes	6
1.3	Ballistic Transport	7
1.3.1	Landauer–Büttiker Formalism	7
1.3.2	Split-Gate Point Contact	9
1.4	Weak Localization	13
1.4.1	Basic Principles	14
1.4.2	Weak Localization in One and Two Dimensions	15
1.4.3	Weak Localization in a Magnetic Field	16
1.5	Spin-Effects: Weak Antilocalization	19
1.6	Al'tshuler–Aronov–Spivak Oscillations	21
1.7	The Aharonov–Bohm Effect	23
1.8	Universal Conductance Fluctuations	27
1.8.1	Basic Principles	27
1.8.2	Detailed Analysis	29
1.8.3	Fluctuations in Long Wires	31
1.8.4	Energy and Temperature Dependence	32
1.9	Concluding Remarks	33
	References	34

2	Charge Transport and Single-Electron Effects in Nanoscale Systems	37
	<i>Joseph M. Thijssen and Herre S.J. van der Zant</i>	
2.1	Introduction: Three-Terminal Devices and Quantization	37
2.2	Description of Transport	40
2.2.1	Structure of Nanoscale Devices	40
2.2.1.1	The Reservoirs	40
2.2.1.2	The Leads	41
2.2.1.3	The Island	41
2.2.2	Transport	42
2.2.2.1	Coherent-Incoherent Transport	43
2.2.2.2	Elastic-Inelastic Transport	44
2.2.2.3	Resonant-Off-Resonant Transport	44
2.2.2.4	First-Order versus Higher-Order Processes	44
2.2.2.5	Direct Tunneling	45
2.3	Resonant Transport	45
2.4	Constant Interaction Model	49
2.5	Charge Transport Measurements as a Spectroscopic Tool	53
2.5.1	Electronic Excitations	55
2.5.2	Including Vibrational States	57
2.6	Second-Order Processes	59
2.6.1	The Kondo Effect in a Quantum Dot with an Unpaired Electron	60
2.6.2	Inelastic Co-Tunneling	61
	References	63
3	Spin Injection–Extraction Processes in Metallic and Semiconductor Heterostructures	65
	<i>Alexander M. Bratkovsky</i>	
3.1	Introduction	65
3.2	Main Spintronic Effects and Devices	67
3.2.1	TMR	67
3.2.2	GMR	68
3.2.3	(Pseudo)Spin-Torque Domain Wall Switching in Nanomagnets	70
3.3	Spin-Orbital Coupling and Electron Interference	
	Semiconductor Devices	72
3.3.1	Spin-Hall Effect (SHE) and Magnetoresistance due to Edge Spin Accumulation	74
3.3.2	Interacting Spin Logic Circuits	76
3.4	Tunnel Magnetoresistance	77
3.4.1	Impurity Suppression of TMR	80
3.4.2	Negative Resonant TMR?	81
3.4.3	Tunneling in Half-Metallic Ferromagnetic Junctions	82
3.4.4	Surface States Assisted TMR	84
3.4.5	Inelastic Effects in TMR	84
3.5	Spin Injection/Extraction into (from) Semiconductors	86
3.5.1	Spin Tunneling through Modified (Delta-Doped) Schottky Barrier	89

3.5.2	Conditions for Efficient Spin Injection and Extraction	95
3.5.3	High-Frequency Spin-Valve Effect	97
3.5.4	Spin-Injection Devices	99
3.5.5	Spin Source of Polarized Radiation	101
3.6	Conclusions	104
	References	104
4	Physics of Computational Elements	109
	<i>Victor V. Zhirnov and Ralph K. Cavin</i>	
4.1	The Binary Switch as a Basic Information-Processing Element	109
4.1.1	Information and Information Processing	109
4.1.2	Properties of an Abstract Binary Information-Processing System	110
4.2	Binary State Variables	111
4.2.1	Essential Operations of an Abstract Binary Switch	111
4.2.2	The Use of Particles to Represent Binary Information	111
4.3	Energy Barriers in Binary Switches	113
4.3.1	Operation of Binary Switches in the Presence of Thermal Noise	113
4.3.2	Quantum Errors	114
4.3.3	A Combined Effect of Classical and Quantum Errors	116
4.4	Energy Barrier Framework for the Operating Limits of Binary Switches	116
4.4.1	Limits on Energy	116
4.4.2	Limits on Size	117
4.4.3	Limits on Speed	118
4.4.4	Energy Dissipation by Computation	119
4.5	Physics of Energy Barriers	119
4.5.1	Energy Barrier in Charge-Based Binary Switch	120
4.5.2	Energy Barrier in Spin-Based Binary Switch	124
4.5.3	Energy Barriers for Multiple-Spin Systems	128
4.5.4	Energy Barriers for the Optical Binary Switch	130
4.6	Conclusions	131
	References	132
II	Nanofabrication Methods	135
5	Charged-Particle Lithography	137
	<i>Lothar Berger, Johannes Kretz, Dirk Beyer, and Anatol Schwersenz</i>	
5.1	Survey	137
5.2	Electron Beam Lithography	141
5.2.1	Introduction	141
5.2.1.1	Electron Sources	141
5.2.1.2	Electron Optics	142
5.2.1.3	Gaussian Beam Lithography	147
5.2.1.4	Shaped Beam Lithography	148
5.2.1.5	Patterning	151

5.2.2	Resists	153
5.2.3	Applications	158
5.2.3.1	Photolithography Masks	158
5.2.3.2	Direct-Write Lithography	162
5.2.3.3	Maskless Lithography	164
5.2.3.4	Imprint Templates	170
5.2.4	Integration	170
5.3	Ion Beam Lithography	172
5.3.1	Introduction	172
5.3.1.1	Ion Sources	173
5.3.1.2	Ion Optics	173
5.3.1.3	Patterning	173
5.3.2	Applications	173
5.3.2.1	Direct-Structuring Lithography	174
5.3.2.2	Imprint Templates	176
5.4	Conclusions	176
	References	177
6	Extreme Ultraviolet Lithography	181
	<i>Klaus Bergmann, Larissa Juschkin, and Reinhart Poprawe</i>	
6.1	Introduction	181
6.1.1	General Aspects	181
6.1.2	System Architecture	182
6.2	The Components of EUV Lithography	185
6.2.1	Light Sources	185
6.2.1.1	Plasmas as EUV Radiators	186
6.2.1.2	Laser-Induced Plasmas	187
6.2.1.3	Gas Discharge Plasmas	188
6.2.1.4	Source Concepts and Current Status	189
6.2.2	Collectors and Debris Mitigation	191
6.2.3	Multilayer Optics	194
6.2.4	Masks	198
6.2.5	Resist	199
6.3	Outlook	203
	References	204
7	Non-Optical Lithography	209
	<i>Clivia M. Sotomayor Torres and Jouni Ahopelto</i>	
7.1	Introduction	209
7.2	Nanoimprint Lithography	210
7.2.1	The Nanoimprint Process	210
7.2.2	Polymers for Nanoimprint Lithography	211
7.2.3	Variations of NIL Methods	215
7.2.3.1	Single-Step NIL	215

7.2.3.2	Step-and-Stamp Imprint Lithography	216
7.2.3.3	Step-and-Flash Imprint Lithography	216
7.2.3.4	Roll-to-Roll Printing	217
7.2.4	Stamps	217
7.2.5	Residual Layer and Critical Dimensions	222
7.2.6	Towards 3-D Nanoimprinting	227
7.2.7	The State of the Art	230
7.3	Discussion	230
7.4	Conclusions	234
	References	235
8	Nanomanipulation with the Atomic Force Microscope	239
	<i>Ari Requicha</i>	
8.1	Introduction	239
8.2	Principles of Operation of the AFM	242
8.2.1	The Instrument and its Modes of Operation	242
8.2.2	Spatial Uncertainties	247
8.3	Nanomanipulation: Principles and Approaches	250
8.3.1	LMR Nanomanipulation by Pushing	250
8.3.2	Other Approaches	253
8.3.3	Manipulation and Assembly of Nanostructures	256
8.4	Manipulation Systems	260
8.4.1	Interactive Systems	260
8.4.2	Automated Systems	261
8.5	Conclusion and Outlook	265
	References	267
9	Harnessing Molecular Biology to the Self-Assembly of Molecular-Scale Electronics	275
	<i>Uri Sivan</i>	
9.1	Introduction	275
9.2	DNA-Templated Electronics	278
9.2.1	Scaffolds and Metallization	278
9.2.2	Sequence-Specific Molecular Lithography	281
9.2.3	Self-Assembly of a DNA-Templated Carbon Nanotube Field-Effect Transistor	284
9.3	Recognition of Electronic Surfaces by Antibodies	288
9.4	Molecular Shift-Registers and their Use as Autonomous DNA Synthesizers [11]	293
9.4.1	Molecular Shift-Registers	293
9.4.2	Error Suppression and Analogy Between Synthesis and Communication Theory	298
9.5	Future Perspectives	300
	References	301